G(3)

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1.3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value	Unit
		MI	

ORDERING INFORMATION

J CT 12 110 CS

J: JieJie Microelectronics Co., Ltd.

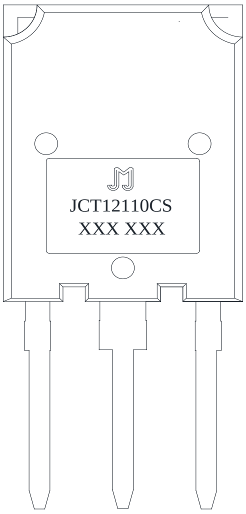
CT: SCRs

12: $V_{DRM}/V_{RRM} \geq 1200V$

110: $I_{T(RMS)}$:110A

CS: CS:TO-247S

MARKING



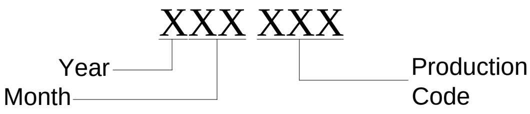


FIG.1: Maximum power dissipation versus RMS on-state current

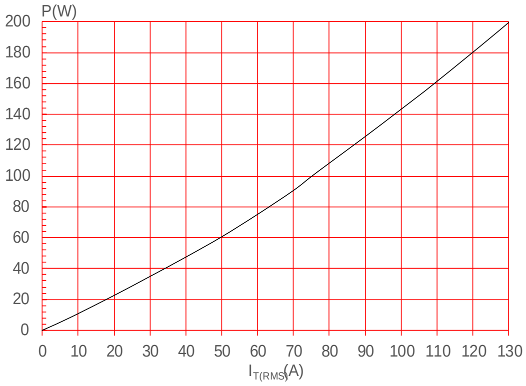


FIG.2: RMS on-state current versus case temperature

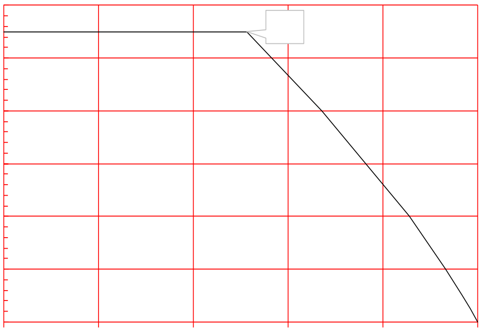
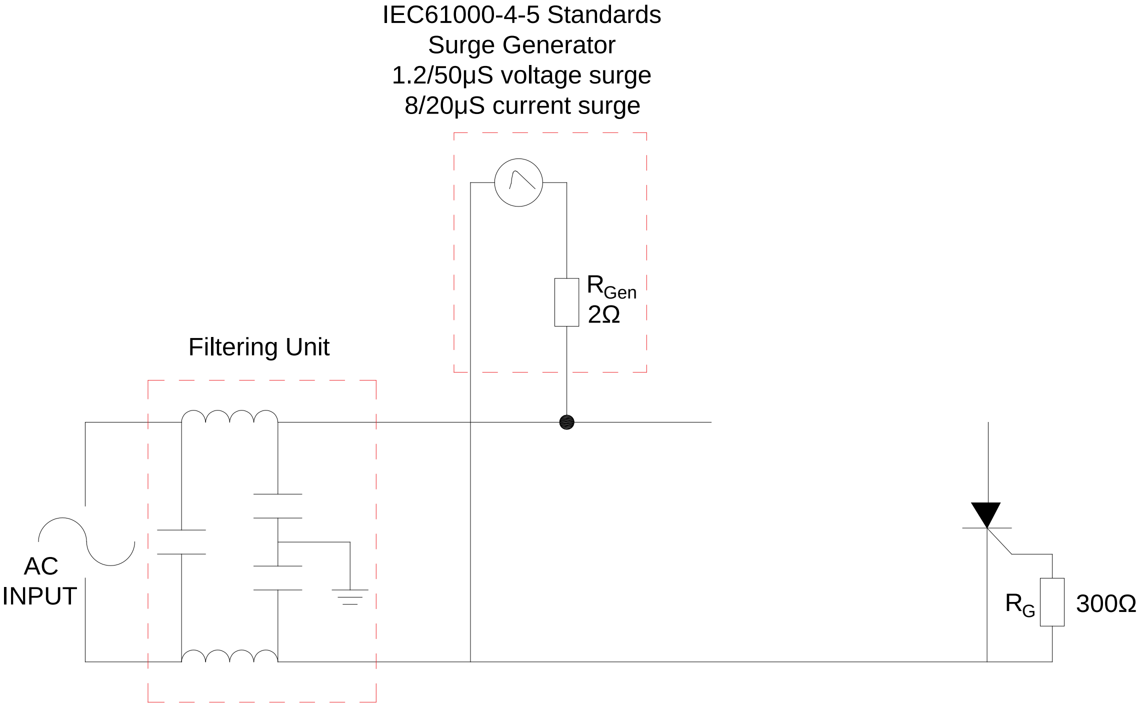


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT12110CS	**1200**	**10-80**	**TO-247S**	**30**	**Tube**

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA